Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	1	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	**Test Condition**	**Quadrant**	**Value**		**Unit**
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	V_D =V_{DRM} T_j =150 R_L =3.3kΩ	- -	MIN.	0.15	V
I_L	I_G =1.2I_{GT}	-	MAX.	70	mA
				80	
I_H	I_T =500mA		MAX.	50	mA
dV/dt	V_D=540V Gate Open T_j =150		MIN.	1000	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j=150		MIN.	18	A/ms
[redacted]	[redacted]	[redacted]	TYP.	10	μs
				80	

ORDERING INFORMATION

T 30 35 H -8 Z

T: Triacs

30: $I_{T(RMS)}$:30A

35: I_{GT1-3} 35mA

H: High junction temperature

-8: 8:V_{DRM} /V_{RRM} 800V

Z: Z:TO-3P(Ins)

MARKING8

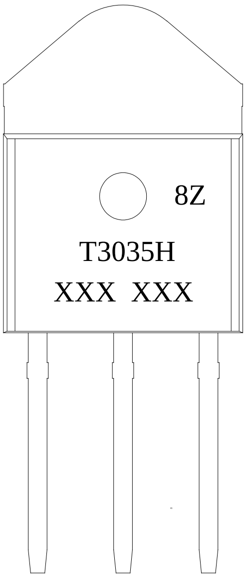


FIG.1: Maxum powpation vMS on-sate c

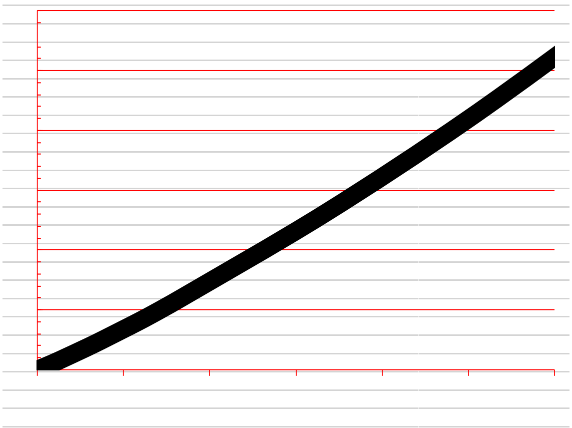


FIG.2: RMS -sate cent v c temper

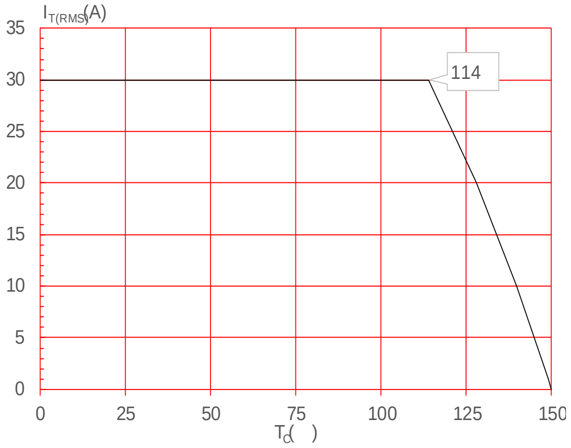
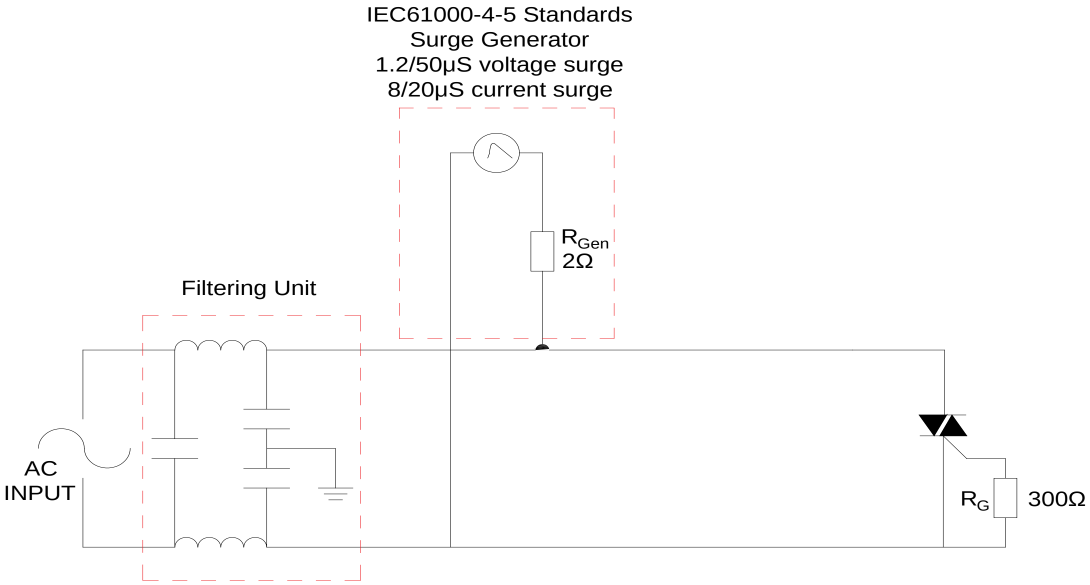


FIG.3: Surge peak on-state current versus number of cycles

FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage V_{DRM} / V_{RRM}

PACKAGE MECHANICAL DATA